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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, FlexIO, I²C, LINbus, SPI, UART/USART
Peripherals	POR, PWM, WDT
Number of I/O	58
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b SAR; D/A1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/fs32k144hft0clht

- Reliability, safety and security
  - HW Security Engine (CSEc)
  - Internal watchdog (WDOG)
  - External Watchdog monitor (EWM) module
  - Error-Correcting Code (ECC) on flash and SRAM memories
  - Cyclic Redundancy Check (CRC) module
  - 128-bit Unique Identification (ID) number
  - System Memory Protection Unit (System MPU)
- Timing and control
  - Up eight independent 16-bit FlexTimers (FTM) module, offering up to 64 standard channels (IC/OC/PWM)
  - One 16-bit Low Power Timer (LPTMR) with flexible wake up control
  - Two Programmable Delay Blocks (PDB) with flexible trigger system
  - One 32-bit Low Power Interrupt Timer (LPIT) with 4 channels
  - 32-bit Real Time Counter (RTC)
- I/O and package
  - 32-pin QFN, 48-pin LQFP, 64-pin LQFP, 100-pin LQFP, MAPBGA-100, 144-pin LQFP, 176-pin LQFP package options
- 16 channel DMA with up to 63 request sources using DMAMUX

1 Block diagram

Following figures show superset high level architecture block diagrams of S32K14x series and S32K11x series respectively. Other devices within the family have a subset of the features. See Feature comparison for chip specific values.

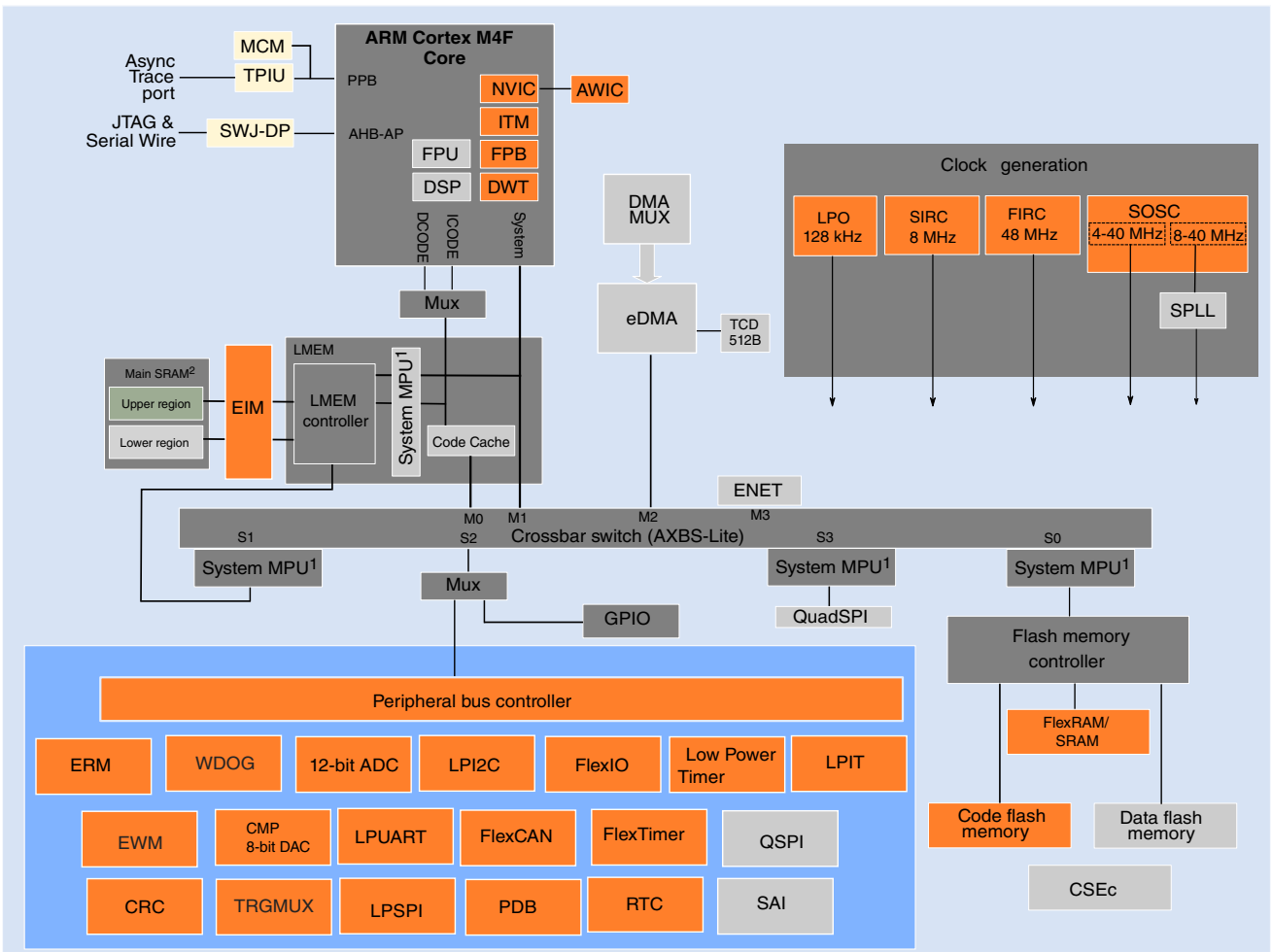
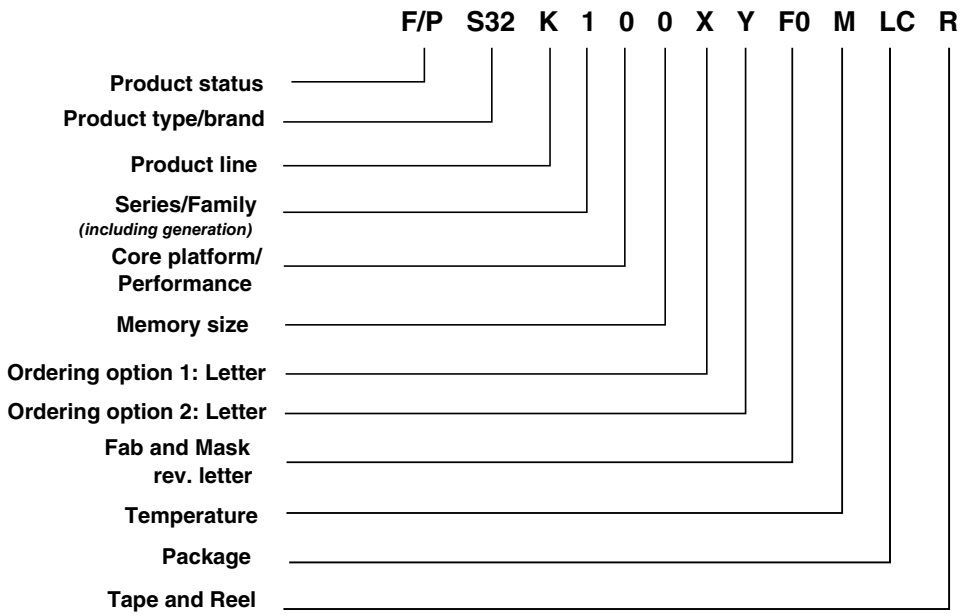


Figure 1. High-level architecture diagram for the S32K14x family

3.2 Ordering information



Product status
P: Prototype
F: Qualified ordering P/N

Product type/brand
S32: Automotive 32-bit MCU

Product line
K: ARM Cortex MCUs
M: MagniV/Mixed Signal

Series/Family
1: 1st product series
2: 2nd product series

Core platform/Performance
1: ARM Cortex M0+
4: ARM Cortex M4F

Memory size

	2	4	6	8
M0+	32 K	64 K	128 K	256 K
M4F	256 K	512 K	1 M	2 M

Ordering option
X: Speed
B: 48 MHz without DMA (only for S32K11x)
L: 48 MHz with DMA (only for S32K11x)
M: 64 MHz
H: 80 MHz
U: 112 MHz

Y: Optional feature
N: No/None
R: Max. RAM
F: CAN-FD and FlexIO including max. RAM
S: Security including max. RAM
A: CAN-FD, FlexIO, and Security including max. RAM
E: Ethernet and audio including max. RAM
J: CAN FD, FlexIO, Security, Ethernet and audio including max. RAM

Fab and Mask rev. letter
Fx: ATMC
Tx: GF
XX: Flex #

x0: 1st fab revision
x1: 2nd fab revision

Temperature
C: -40C to 85C
V: -40C to 105C
M: -40C to 125C

Package

Pins	LQFP	LQFP -EP	QFN	BGA
32	LC	-	FM	-
48	LF	KF	FT	-
64	LH	KH	-	-
100	LL	-	-	MH
144	LQ	-	-	-
176	LU	-	-	-

Tape and Reel
T: Trays and Tubes
R: Tape and Reel

Figure 4. Ordering information

Table 10. DC electrical specifications at 5.0 V Range (continued)

Symbol	Parameter	Value			Unit	Notes
		Min.	Typ.	Max.		
Ioh_Strong	I/O current source capability measured when pad = V_{DDE} - 0.8 V	20	—	—	mA	3, 4
Iol_Strong	I/O current sink capability measured when pad = 0.8 V	20	—	—	mA	4, 5
IOHT	Output high current total for all ports	—	—	100	mA	
IIN	Input leakage current (per pin) for full temperature range at V_{DD} = 5.5 V					6
	All pins other than high drive port pins		0.005	0.5	µA	
	High drive port pins		0.010	0.5	µA	
R_{PU}	Internal pullup resistors	20		50	kΩ	7
R_{PD}	Internal pulldown resistors	20		50	kΩ	8

1. For reset pads, same V_{ih} levels are applicable
2. For reset pads, same V_{il} levels are applicable
3. The value given is measured at high drive strength mode. For value at low drive strength mode see the Ioh_Standard value given above.
4. The strong pad I/O pin is capable of switching a 50 pF load at up to 40 MHz.
5. The value given is measured at high drive strength mode. For value at low drive strength mode see the Iol_Standard value given above.
6. Several I/O have both high drive and normal drive capability selected by the associated Portx_PCRn[DSE] control bit. All other GPIOs are normal drive only. For details refer to *SK3K144_IO_Signal_Description_Input_Multiplexing.xlsx* attached with the *Reference Manual*.
7. Measured at input V = V_{SS}
8. Measured at input V = V_{DD}

5.5 AC electrical specifications at 3.3 V range

Table 11. AC electrical specifications at 3.3 V Range

Symbol	DSE	Rise time (nS) [1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max.	Min.	Max.	
Standard	NA	4.6	14.5	3.9	15.7	25
		7.2	23.7	6.2	26.2	50
		24.0	75.4	20.8	88.4	200
Strong	0	4.6	14.5	3.9	15.7	25
		7.2	23.7	6.2	26.2	50
		24.0	75.4	20.8	88.4	200
	1	2.0	5.8	1.8	6.1	25
		2.8	8.0	2.6	8.3	50
		7.0	20.7	6.0	22.4	200

1. For reference only. Run simulations with the IBIS model and your custom board for accurate results.
2. Maximum capacitances supported on Standard IOs. However interface or protocol specific specifications might be different, for example for ENET, QSPI etc. . For protocol specific AC specifications, see respective sections.

5.6 AC electrical specifications at 5 V range

Table 12. AC electrical specifications at 5 V Range

Symbol	DSE	Rise time (nS)[1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max .	Min.	Max.	
Standard	NA	3.2	9.4	3.6	10.7	25
		5.4	15.7	5.1	17.4	50
		18.5	52.6	17.6	59.7	200
Strong	0	4.0	9.4	3.6	10.7	25
		5.8	15.7	5.1	17.4	50
		18.1	52.6	17.6	59.7	200
	1	1.6	4.6	1.5	5.0	25
		2.2	5.7	2.2	5.8	50
		5.6	14.6	5.0	15.4	200

1. For reference only. Run simulations with the IBIS model and your custom board for accurate results.
2. Maximum capacitances supported on Standard IOs. However interface or protocol specific specifications might be different, for example for ENET, QSPI etc. . For protocol specific AC specifications, see respective sections.

5.7 Standard input pin capacitance

Table 13. Standard input pin capacitance

Symbol	Description	Min.	Max.	Unit
C_{IN_D}	Input capacitance: digital pins	—	7	pF

NOTE

Please refer to External System Oscillator electrical specifications for EXTAL/XTAL pins.

5.8 Device clock specifications

Table 14. Device clock specifications [1]

Symbol	Description	Min.	Max.	Unit
High Speed run mode[2]				
f_{SYS}	System and core clock	—	112	MHz
f_{BUS}	Bus clock	—	56	MHz
f_{FLASH}	Flash clock	—	28	MHz
Normal run mode (S32K11x series)				

Table continues on the next page...

6.3.1.1 Flash timing specifications — commands

Table 21. Flash command timing specifications

Symbol	Description[1]	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk64k}$ $t_{rd1blk512k}$	Read 1s Block execution time • 64 KB data flash • 512 KB program flash	— —	— —	0.5 1.8	ms ms	
$t_{rd1sec2k}$	Read 1s Section execution time (2 KB flash)	—	—	75	µs	
$t_{rd1sec4k}$	Read 1s Section execution time (4 KB flash)	—	—	100	µs	
t_{pgmchk}	Program Check execution time	—	—	95	µs	
t_{pgm8}	Program Phrase execution time	—	90	150	µs	
$t_{ersblk64k}$ $t_{ersblk512k}$	Erase Flash Block execution time • 64 KB data flash • 512 KB program flash	— —	55 435	475 3700	ms ms	2
t_{ersscr}	Erase Flash Sector execution time	—	15	115	ms	2
$t_{pgmsec1k}$	Program Section execution time (1KB flash)	—	5	—	ms	
$t_{rd1allx}$	Read 1s All Blocks execution time	— — —	— — —	2.2 4.4 6.6	ms ms ms	
t_{rdonce}	Read Once execution time	—	—	30	µs	
$t_{pgmonce}$	Program Once execution time	—	90	—	µs	
t_{ersall}	Erase All Blocks execution time	—	500	4200	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	35	µs	
$t_{ersallu}$	Erase All Blocks Unsecure execution time	—	500	4200	ms	2
$t_{pgmpart32k}$ $t_{pgmpart64k}$	Program Partition for EEPROM execution time • 32 KB EEPROM backup • 64 KB EEPROM backup (Non-Interleaved DFlash) • 64 KB EEPROM backup (Interleaved DFlash)	— —	70 71 250	— —	ms ms ms	3, 4
$t_{setramff}$ $t_{setram32k}$ $t_{setram48k}$ $t_{setram64k}$	Set FlexRAM Function execution time: • Control Code 0xFF • 32 KB EEPROM backup • 48 KB EEPROM backup • 64 KB EEPROM backup	— — — —	70 0.8 1.0 1.3	— 1.2 1.5 1.9	µs ms ms ms	3, 4
$t_{eewr8b32k}$ $t_{eewr8b48k}$ $t_{eewr8b64k}$	Byte-write to FlexRAM execution time: • 32 KB EEPROM backup • 48 KB EEPROM backup • 64 KB EEPROM backup	— — —	385 430 475	1700 1850 2000	µs µs µs	3, 4
$t_{eewr16b32k}$ $t_{eewr16b48k}$	16-bit write to FlexRAM execution time: • 32 KB EEPROM backup	— —	385 430	1700 1850	µs µs	3, 4

Table continues on the next page...

Table 22. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	—	—	years	
$n_{nvmcycp}$	Cycling endurance	1 K	—	—	cycles	2, 1
When using FlexMemory feature: FlexRAM as Emulated EEPROM						
$t_{nvmretee}$	Data retention	5	—	—	years	
$n_{nvmwree16}$ $n_{nvmwree256}$	Write endurance • EEPROM backup to FlexRAM ratio = 16 • EEPROM backup to FlexRAM ratio = 256	100 K 1.6 M	— —	— —	writes writes	3, 4, 5

1. Program and Erase for PFlash and DFlash are supported across product temperature specification in Normal Mode (not supported in HSRUN mode).
2. Cycling endurance is per DFlash or PFlash Sector.
3. FlexMemory write endurance specified for 16-bit and/or 32-bit writes to FlexRAM and is supported across standard temperature specification in Normal Mode (not supported in HSRUN mode). Greater write endurance may be achieved with larger ratios of EEPROM backup to FlexRAM.
4. For usage of any other EEE driver other than the FlexMemory feature, the endurance specification will fall back to the specified endurance value of the D-Flash specification (1 K).
5. EEE calculator tool is available at NXP web site to help estimate the maximum write endurance achievable at specific EEPROM/FlexRAM ratio. The “In Spec” portions of the online calculator refer to the NVM reliability specifications section of data sheet. This calculator is only applies to the FlexMemory feature.

6.3.2 QuadSPI AC specifications

The following table describes the QuadSPI electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.
- Add 50 ohm series termination on board in QuadSPI SCK for Flash A to avoid loop back reflection when using in Internal DQS (PAD Loopback) mode.
- For non-Quad mode of operation if external device doesn’t have pull-up feature, external pull-up needs to be added at board level for non-used pads.
- With external pull-up, performance of the interface may degrade based on load associated with external pull-up.

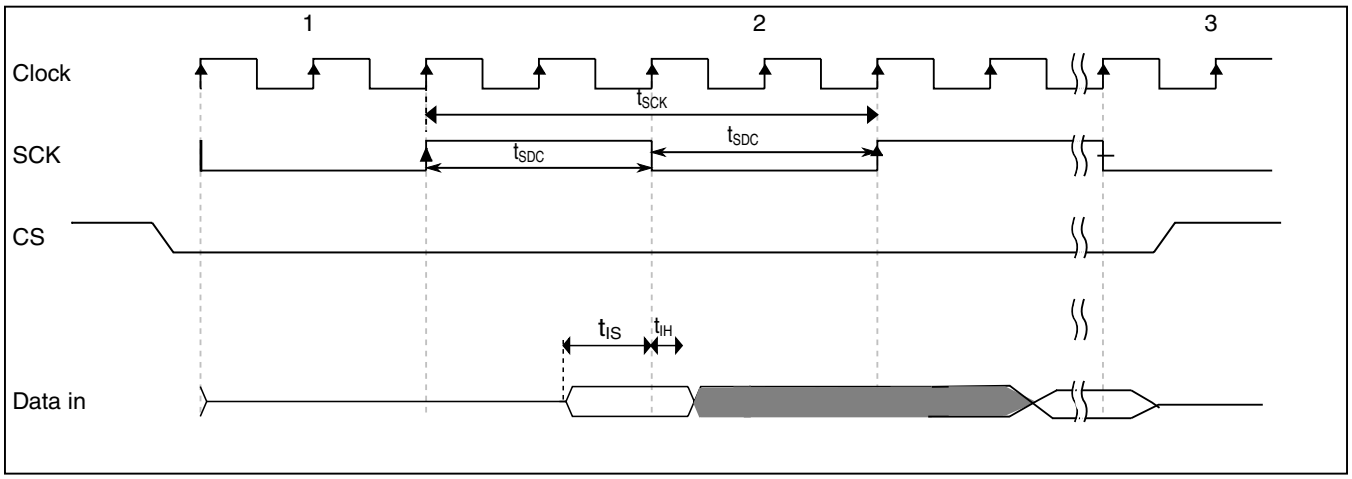


Figure 9. QuadSPI input timing (SDR mode) diagram

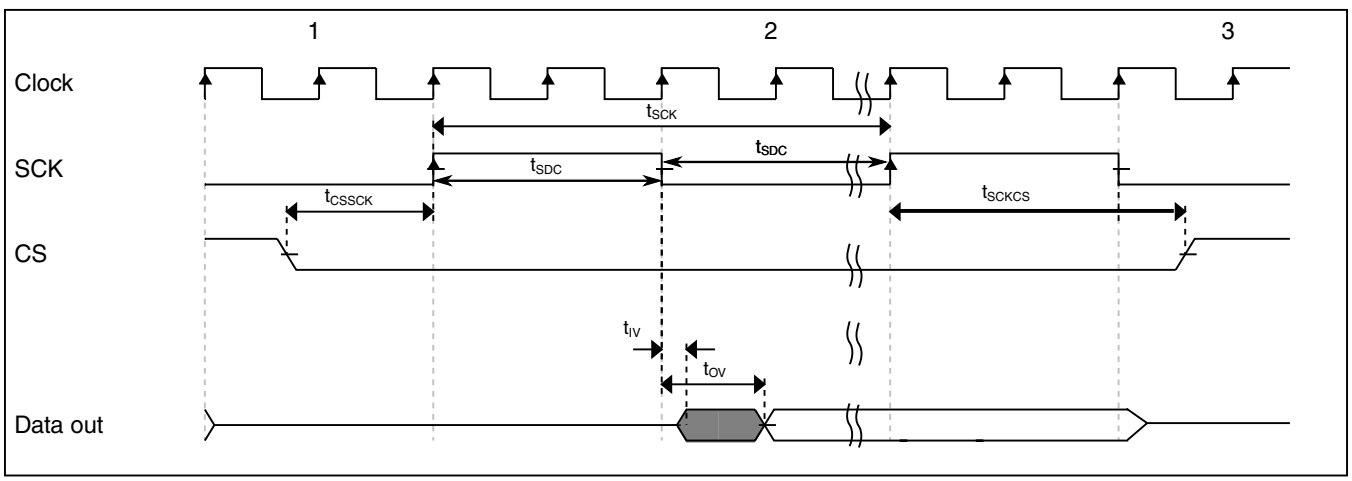


Figure 10. QuadSPI output timing (SDR mode) diagram

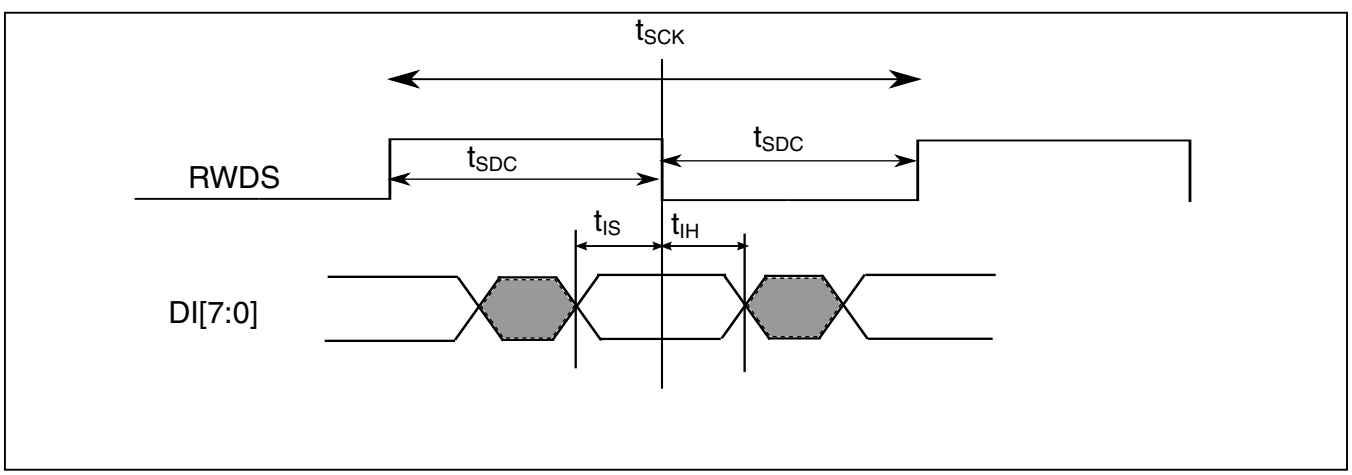


Figure 11. QuadSPI input timing (HyperRAM mode) diagram

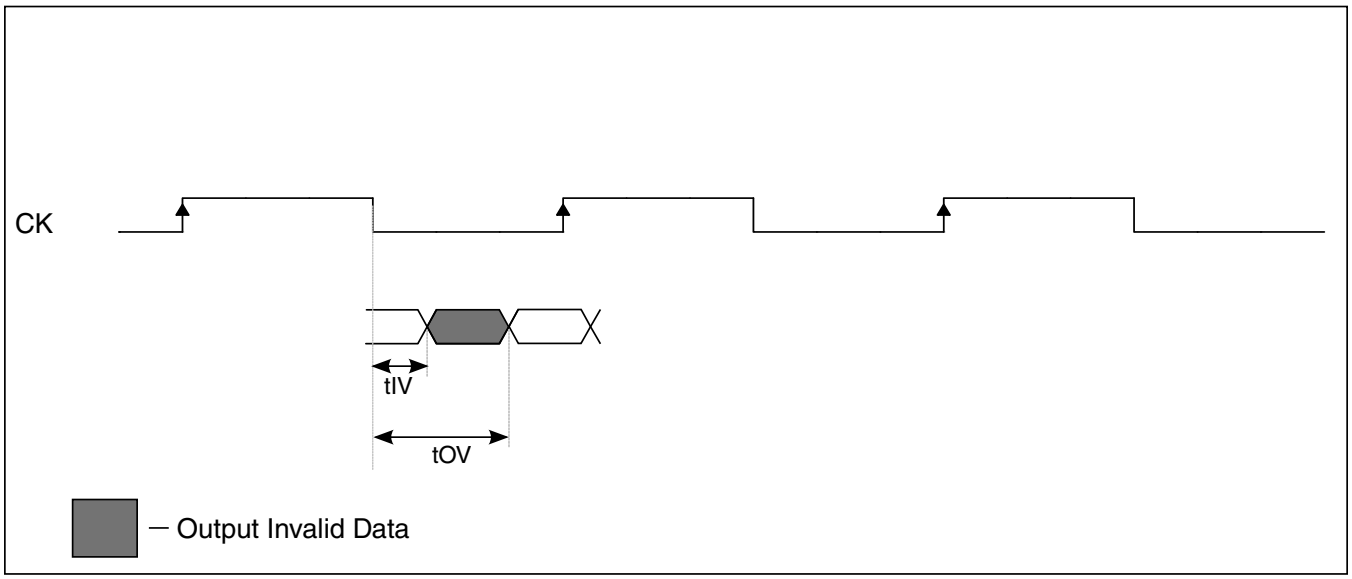


Figure 12. QuadSPI output timing (HyperRAM mode) diagram

6.4 Analog modules

6.4.1 ADC electrical specifications

6.4.1.1 12-bit ADC operating conditions

Table 24. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD} – V_{DDA})	-0.1	0	+0.1	V	2
V_{REFH}	ADC reference voltage high		See Voltage and current operating requirements for values	V_{DDA}	See Voltage and current operating requirements for values	V	3
V_{REFL}	ADC reference voltage low		See Voltage and current operating requirements for values	0	See Voltage and current operating requirements for values	mV	3
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
R_S	Source impedendance	f_{ADCK} < 4 MHz	—	—	5	kΩ	
R_{SW1}	Channel Selection Switch Impedance		—	-0.75	1.2	kΩ	
R_{AD}	Sampling Switch Impedance		—	2	5	kΩ	
C_{P1}	Pin Capacitance		—	10	—	pF	

Table continues on the next page...

Table 28. Comparator with 8-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
V_{AIN}	Analog input voltage	0	0 - V_{DDA}	V_{DDA}	V
V_{AIO}	Analog input offset voltage, High-speed mode				mV
	-40 - 125 °C	-25	±1	25	
V_{AIO}	Analog input offset voltage, Low-speed mode				mV
	-40 - 125 °C	-40	±4	40	
t_{DHSB}	Propagation delay, High-speed mode[2]				ns
	-40 - 105 °C	—	30	200	
	-40 - 125 °C		30	300	
t_{DLSB}	Propagation delay, Low-speed mode[2]				µs
	-40 - 105 °C	—	0.5	2	
	-40 - 125 °C	—	0.5	3	
t_{DHSS}	Propagation delay, High-speed mode[3]				ns
	-40 - 105 °C	—	70	400	
	-40 - 125 °C	—	70	500	
t_{DLSS}	Propagation delay, Low-speed mode[3]				µs
	-40 - 105 °C	—	1	5	
	-40 - 125 °C	—	1	5	
t_{IDHS}	Initialization delay, High-speed mode[4]				µs
	-40 - 125 °C	—	1.5	3	
t_{IDLS}	Initialization delay, Low-speed mode[4]				µs
	-40 - 125 °C	—	10	30	
V_{HYST0}	Analog comparator hysteresis, Hyst0 (V_{AIO})				mV
	-40 - 125 °C	—	0	—	
V_{HYST1}	Analog comparator hysteresis, Hyst1, High-speed mode				mV
	-40 - 125 °C	—	16	66	
	Analog comparator hysteresis, Hyst1, Low-speed mode				
	-40 - 125 °C	—	11	40	
V_{HYST2}	Analog comparator hysteresis, Hyst2, High-speed mode				mV
	-40 - 125 °C	—	32	133	
	Analog comparator hysteresis, Hyst2, Low-speed mode				
	-40 - 125 °C	—	22	80	
V_{HYST3}	Analog comparator hysteresis, Hyst3, High-speed mode				mV
	-40 - 125 °C	—	48	200	
	Analog comparator hysteresis, Hyst3, Low-speed mode				
	-40 - 125 °C	—	33	120	

Table continues on the next page...

Table 28. Comparator with 8-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DAC8b}	8-bit DAC current adder (enabled)				
	3.3V Reference Voltage	—	6	9	µA
	5V Reference Voltage	—	10	16	µA
INL[5]	8-bit DAC integral non-linearity	–0.75	—	0.75	LSB[6]
DNL	8-bit DAC differential non-linearity	–0.5	—	0.5	LSB[6]
t_{DDAC}	Initialization and switching settling time	—	—	30	µs

1. Difference at input > 200mV
2. Applied ± (100 mV + $V_{HYST0/1/2/3}$+ max. of V_{AIO}) around switch point.
3. Applied ± (30 mV + 2 × $V_{HYST0/1/2/3}$+ max. of V_{AIO}) around switch point.
4. Applied ± (100 mV + $V_{HYST0/1/2/3}$).
5. Calculation method used: Linear Regression Least Square Method
6. 1 LSB = $V_{reference}$/256

NOTE

For comparator IN signals adjacent to V_{DD}/V_{SS} or XTAL/EXTAL or switching pins cross coupling may happen and hence hysteresis settings can be used to obtain the desired comparator performance. Additionally, an external capacitor (1nF) should be used to filter noise on input signal. Also, source drive should not be weak (Signal with < 50 K pull up/down is recommended).

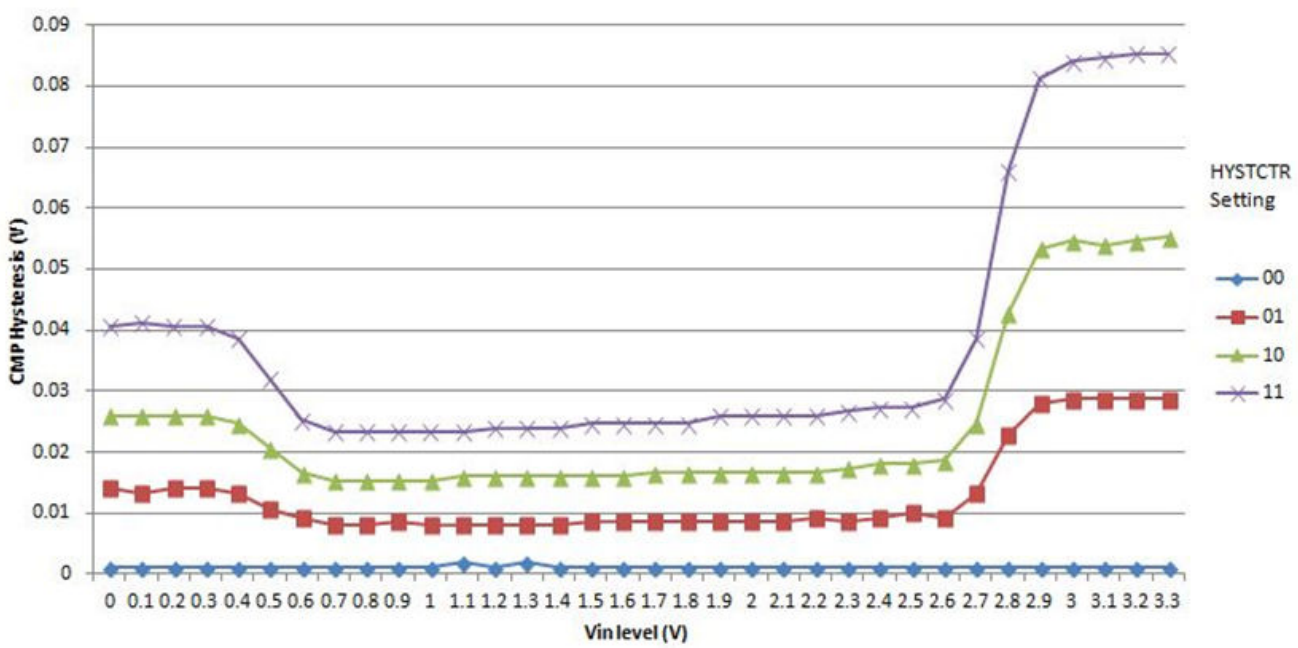


Figure 14. Typical hysteresis vs. Vin level (VDDA = 3.3 V, PMODE = 0)

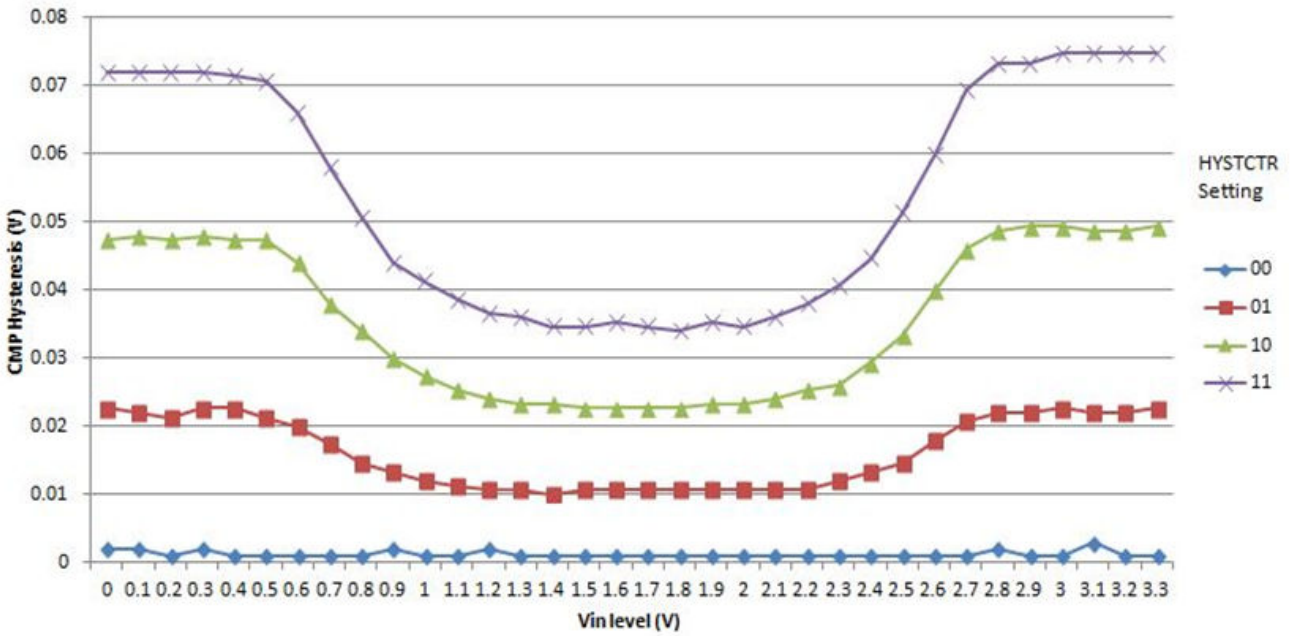


Figure 15. Typical hysteresis vs. Vin level (VDDA = 3.3 V, PMODE = 1)

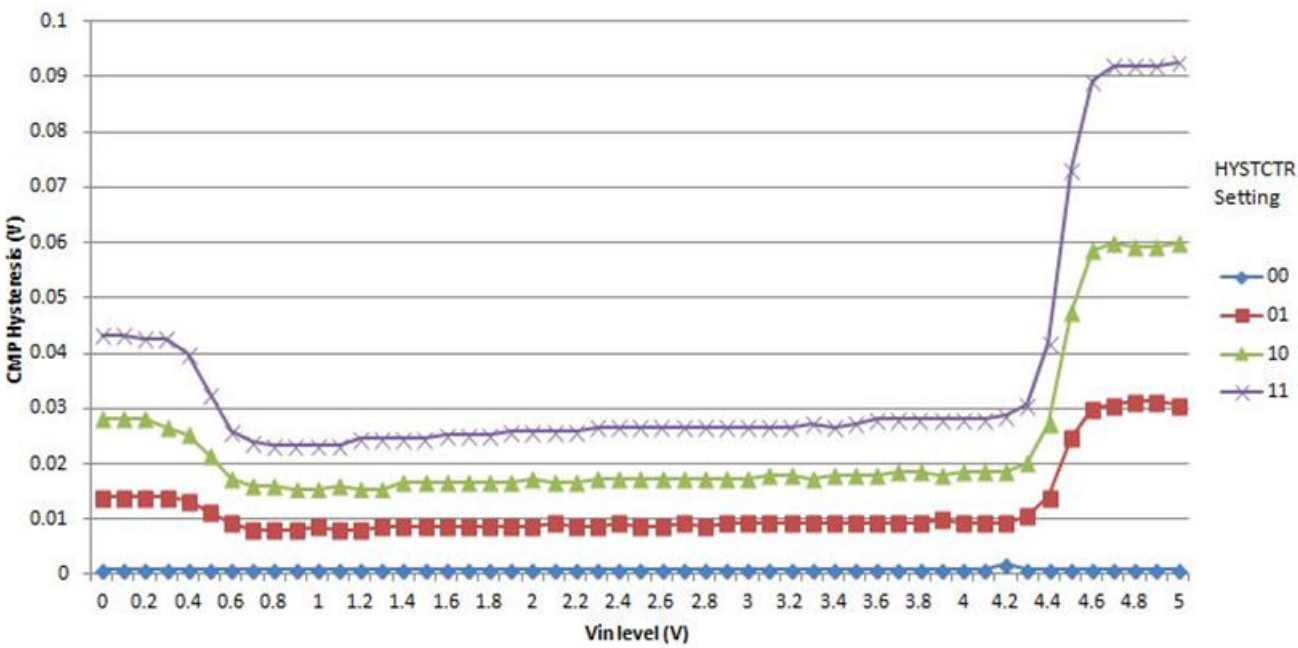


Figure 16. Typical hysteresis vs. Vin level (VDDA = 5 V, PMODE = 0)

Table 29. LPSPI electrical specifications[1] (continued)

Num	Symbol	Description	Conditions	Run Mode[2]				HSRUN Mode[2]				VLPR Mode				Unit
				5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
			Master	(PCSSCK + 1)*t_{SPSCK} - 25	-	(PCSSCK + 1)*t_{SPSCK} - 25	-	(PCSSCK + 1)*t_{SPSCK} - 25	-	(PCSSCK + 1)*t_{SPSCK} - 25	-	(PCSSCK + 1)*t_{SPSCK} - 50	-	(PCSSCK + 1)*t_{SPSCK} - 50	-	
			Master Loopback[5]													
			Master Loopback(slow) [6]													
4	t_{Lag}[8]	Enable lag time (After SPSCK delay)	Slave	-	-	-	-	-	-	-	-	-	-	-	-	ns
			Master	(SCKPCS + 1)*t_{SPSCK} - 25	-	(SCKPCS + 1)*t_{SPSCK} - 25	-	(SCKPCS + 1)*t_{SPSCK} - 25	-	(SCKPCS + 1)*t_{SPSCK} - 25	-	(SCKPCS + 1)*t_{SPSCK} - 50	-	(SCKPCS + 1)*t_{SPSCK} - 50	-	
			Master Loopback[5]													
			Master Loopback(slow) [6]													

Table continues on the next page...

Table 29. LPSPI electrical specifications[1] (continued)

Num	Symbol	Description	Conditions	Run Mode[2]				HSRUN Mode[2]				VLPR Mode				Unit
				5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
5	t_{WSPSCK}	Clock(SPSCK) high or low time (SPSCK duty cycle)	Slave	$t_{SPSCK}/2 - 3$	$t_{SPSCK}/2 + 3$	$t_{SPSCK}/2 - 3$	$t_{SPSCK}/2 + 3$	$t_{SPSCK}/2 - 3$	$t_{SPSCK}/2 + 3$	$t_{SPSCK}/2 - 3$	$t_{SPSCK}/2 + 3$	$t_{SPSCK}/2 - 5$	$t_{SPSCK}/2 + 5$	$t_{SPSCK}/2 - 5$	$t_{SPSCK}/2 + 5$	ns
			Master													
			Master Loopback[5]													
			Master Loopback(slow) [6]													
6	t_{SU}	Data setup time(inputs)	Slave	3	-	5	-	3	-	5	-	18	-	18	-	ns
			Master	29	-	38	-	26	-	37	-	72	-	78	-	
			Master Loopback[5]	7	-	8	-	5	-	7	-	20	-	20	-	
			Master Loopback(slow) [6]	8	-	10	-	7	-	9	-	20	-	20	-	
7	t_{HI}	Data hold time(inputs)	Slave	3	-	3	-	3	-	3	-	14	-	14	-	ns
			Master	0	-	0	-	0	-	0	-	0	-	0	-	
			Master Loopback[5]	3	-	3	-	2	-	3	-	11	-	11	-	
			Master Loopback(slow) [6]	3	-	3	-	3	-	3	-	12	-	12	-	
8	t_a	Slave access time	Slave	-	50	-	50	-	50	-	50	-	100	-	100	ns
9	t_{dis}	Slave MISO (SOUT) disable time	Slave	-	50	-	50	-	50	-	50	-	100	-	100	ns

Table continues on the next page...

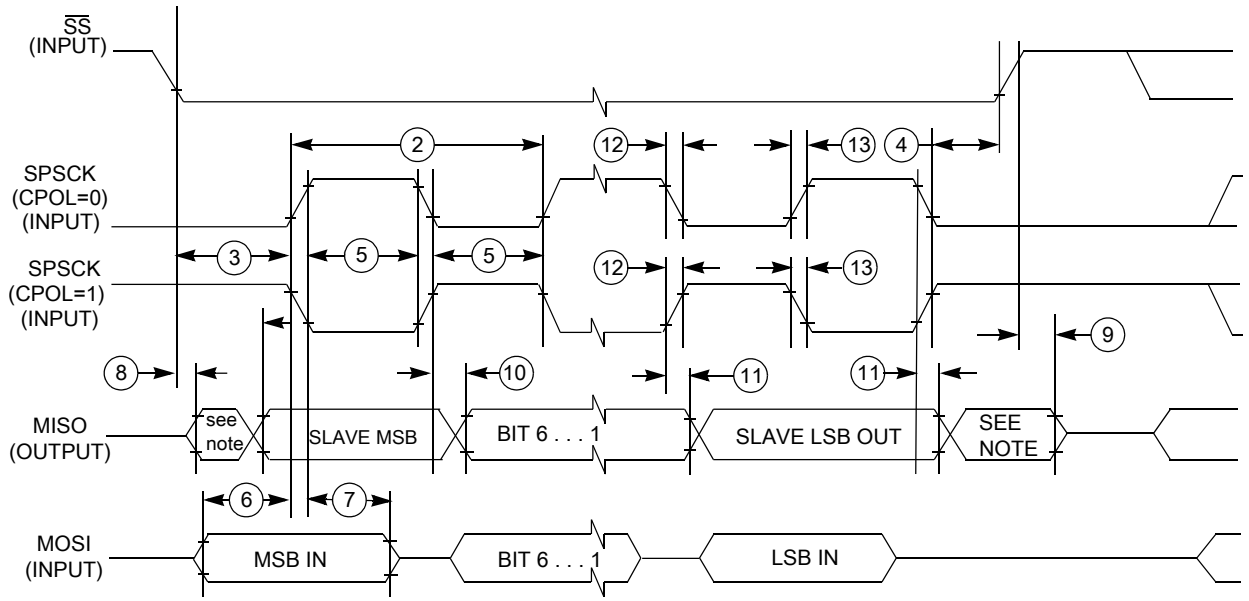


Figure 20. LPSPI slave mode timing (CPHA = 0)

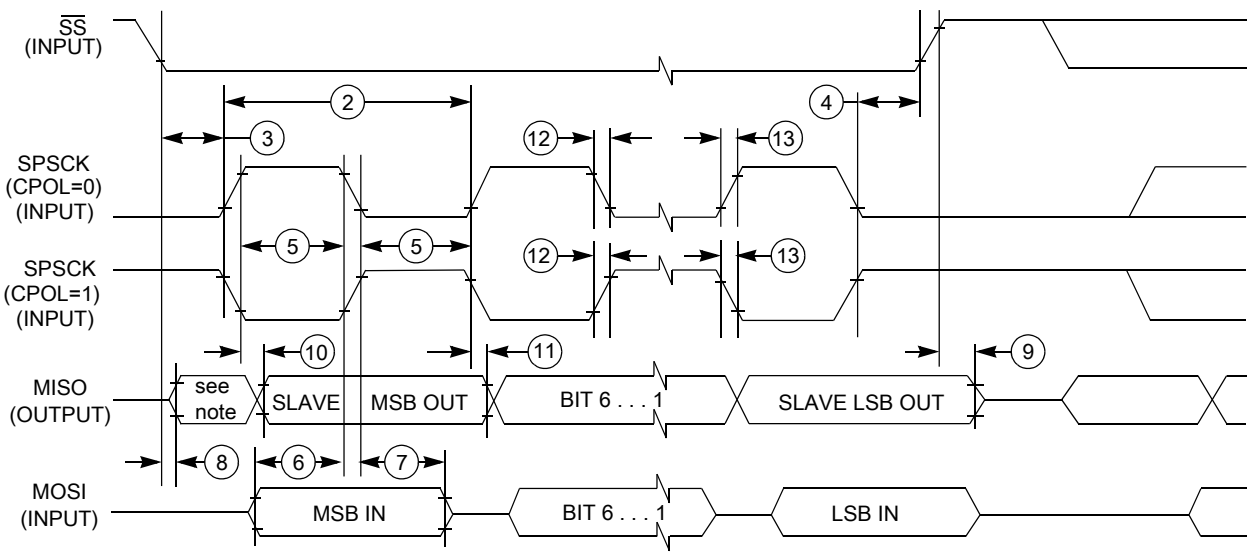


Figure 21. LPSPI slave mode timing (CPHA = 1)

6.5.3 LPI2C electrical specifications

See General AC specifications for LPI2C specifications.

For supported baud rate see section 'Chip-specific LPI2C information' of the *Reference Manual.*

6.5.4 FlexCAN electical specifications

For supported baud rate, see section 'Protocol timing' of the *Reference Manual*.

6.5.5 SAI electrical specifications

The following table describes the SAI electrical characteristics.

- Measurements are with maximum output load of 50 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.

Table 30. Master mode timing specifications

Symbol	Description	Min.	Max.	Unit
—	Operating voltage	2.97	3.6	V
S1	SAI_MCLK cycle time	40	—	ns
S2	SAI_MCLK pulse width high/low	45%	55%	MCLK period
S3	SAI_BCLK cycle time	80	—	ns
S4	SAI_BCLK pulse width high/low	45%	55%	BCLK period
S5	SAI_RXD input setup before SAI_BCLK	28	—	ns
S6	SAI_RXD input hold after SAI_BCLK	0	—	ns
S7	SAI_BCLK to SAI_TXD output valid	—	8	ns
S8	SAI_BCLK to SAI_TXD output invalid	-2	—	ns
S9	SAI_FS input setup before SAI_BCLK	28	—	ns
S10	SAI_FS input hold after SAI_BCLK	0	—	ns
S11	SAI_BCLK to SAI_FS output valid	—	8	ns
S12	SAI_BCLK to SAI_FS output invalid	-2	—	ns

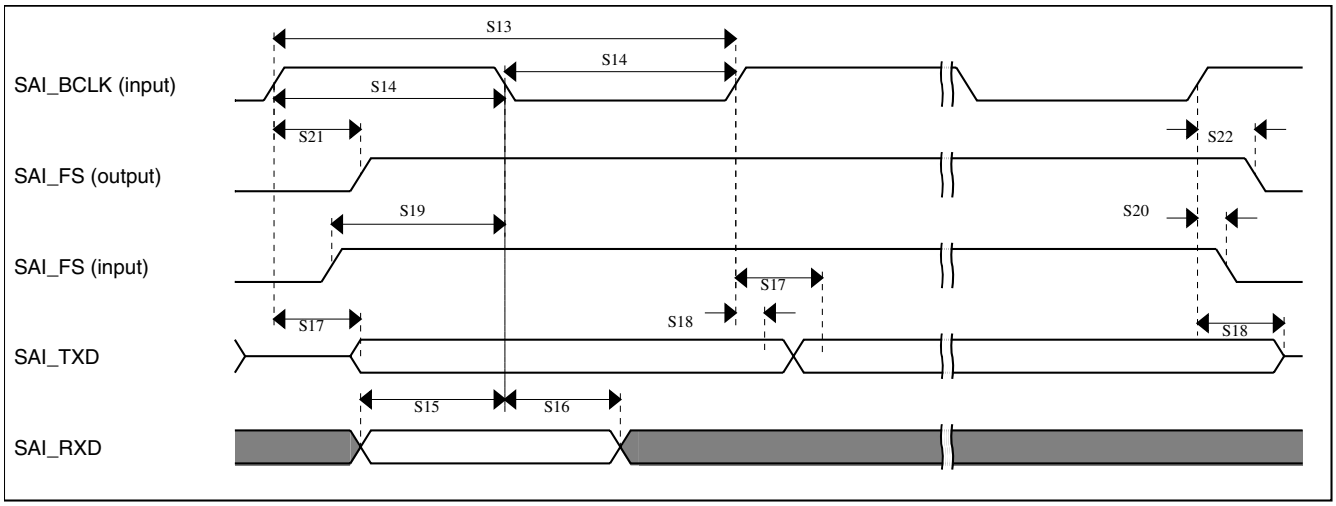


Figure 23. SAI Timing — Slave modes

6.5.6 Ethernet AC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

The following table describes the MII electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.

Table 32. MII signal switching specifications

Symbol	Description	Min.	Max.	Unit
—	RXCLK frequency	—	25	MHz
MII1	RXCLK pulse width high	35%	65%	RXCLK period
MII2	RXCLK pulse width low	35%	65%	RXCLK period
MII3	RXD[3:0], RXDV, RXER to RXCLK setup	5	—	ns
MII4	RXCLK to RXD[3:0], RXDV, RXER hold	5	—	ns
—	TXCLK frequency	—	25	MHz
MII5	TXCLK pulse width high	35%	65%	TXCLK period
MII6	TXCLK pulse width low	35%	65%	TXCLK period
MII7	TXCLK to TXD[3:0], TXEN, TXER invalid	2	—	ns
MII8	TXCLK to TXD[3:0], TXEN, TXER valid	—	25	ns

Table 33. RMII signal switching specifications (continued)

Symbol	Description	Min.	Max.	Unit
RMII7	RMII_CLK to TXD[1:0], TXEN invalid	2	—	ns
RMII8	RMII_CLK to TXD[1:0], TXEN valid	—	15	ns

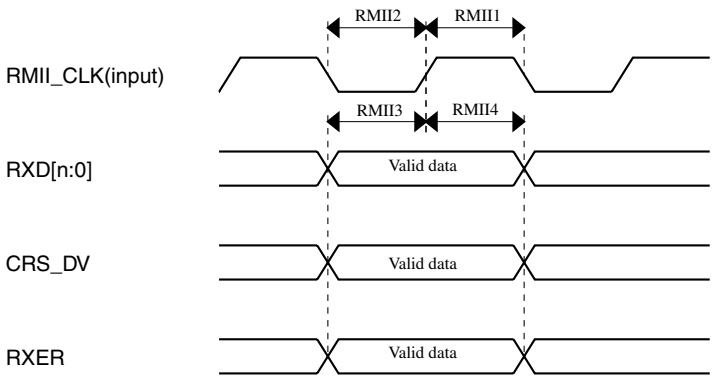


Figure 26. RMII receive diagram

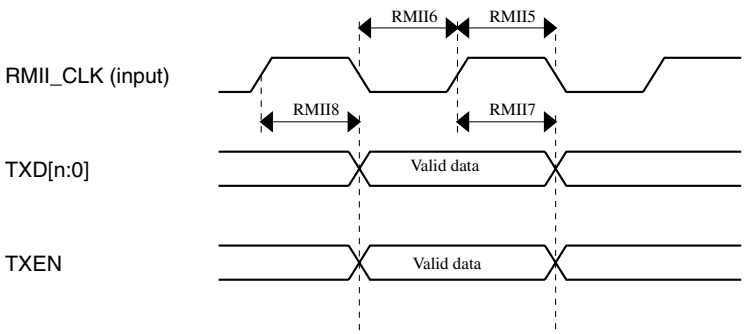


Figure 27. RMII transmit diagram

The following table describes the MDIO electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.
- MDIO pin must have external Pull-up.

Table 34. MDIO timing specifications

Symbol	Description	Min.	Max.	Unit
—	MDC Clock Frequency	—	2.5	MHz

Table continues on the next page...

Table 34. MDIO timing specifications (continued)

Symbol	Description	Min.	Max.	Unit
MDC1	MDC pulse width high	40%	60%	MDC period
MDC2	MDC pulse width low	40%	60%	MDC period
MDC3	MDIO (input) to MDC rising edge setup	25	—	ns
MDC4	MDIO (input) to MDC rising edge hold	0	—	ns
MDC5	MDC falling edge to MDIO output valid (maximum propagation delay)	—	25	ns
MDC6	MDC falling edge to MDIO output invalid (minimum propagation delay)	-10	—	ns

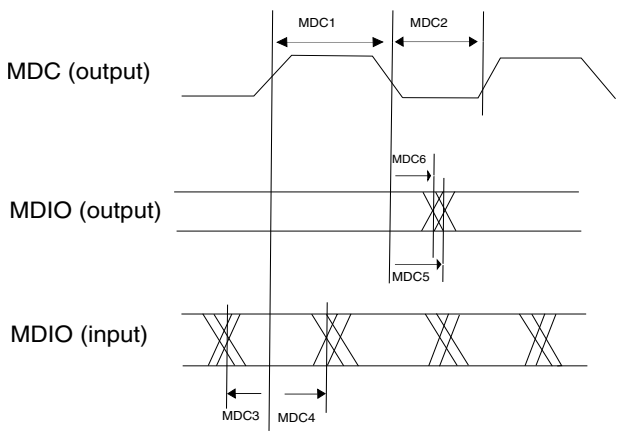


Figure 28. MII/RMII serial management channel timing diagram

6.5.7 Clockout frequency

Maximum supported clock out frequency for this device is 20 MHz

6.6 Debug modules

6.6.1 SWD electrical specofications

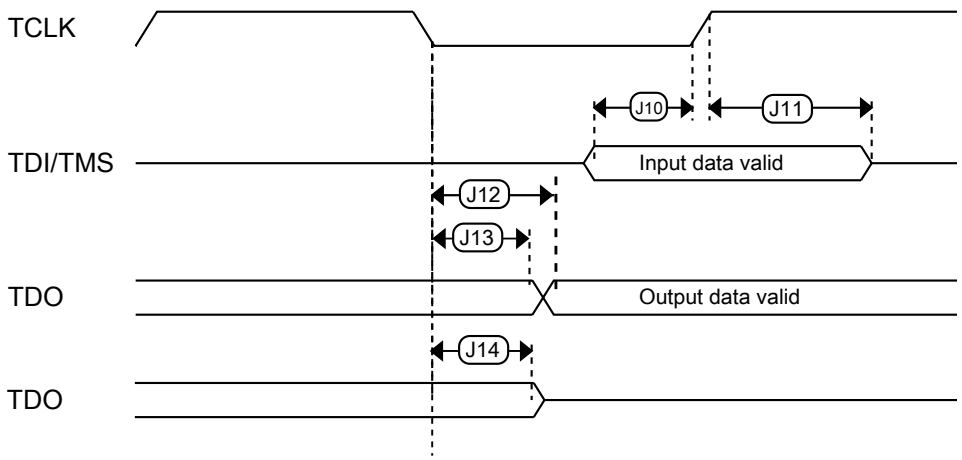


Figure 34. Test Access Port timing

7 Thermal attributes

7.1 Description

The tables in the following sections describe the thermal characteristics of the device.

NOTE

Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting side (board) temperature, ambient temperature, air flow, power dissipation or other components on the board, and board thermal resistance.

7.2 Thermal characteristics